

# XN06501G

## Silicon NPN epitaxial planar type

For general amplification

### ■ Features

- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

### ■ Basic Part Number

- 2SD0601A × 2

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter                             | Symbol           | Rating      | Unit             |
|---------------------------------------|------------------|-------------|------------------|
| Collector-base voltage (Emitter open) | $V_{\text{CBO}}$ | 60          | V                |
| Collector-emitter voltage (Base open) | $V_{\text{CEO}}$ | 50          | V                |
| Emitter-base voltage (Collector open) | $V_{\text{EBO}}$ | 7           | V                |
| Collector current                     | $I_{\text{C}}$   | 100         | mA               |
| Peak collector current                | $I_{\text{CP}}$  | 200         | mA               |
| Total power dissipation               | $P_{\text{T}}$   | 300         | mW               |
| Junction temperature                  | $T_{\text{j}}$   | 150         | $^\circ\text{C}$ |
| Storage temperature                   | $T_{\text{stg}}$ | -55 to +150 | $^\circ\text{C}$ |

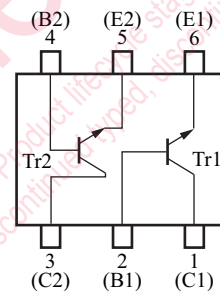
### ■ Package

- Code  
Mini6-G3
- Pin Name
 

|                    |                  |
|--------------------|------------------|
| 1: Collector (Tr1) | 4: Base (Tr2)    |
| 2: Base (Tr1)      | 5: Emitter (Tr2) |
| 3: Collector (Tr2) | 6: Emitter (Tr1) |

### ■ Marking Symbol: 5N

### ■ Internal Connection

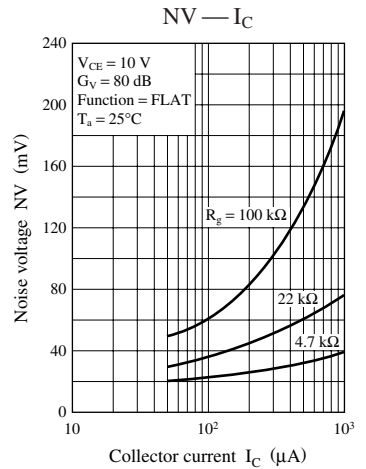
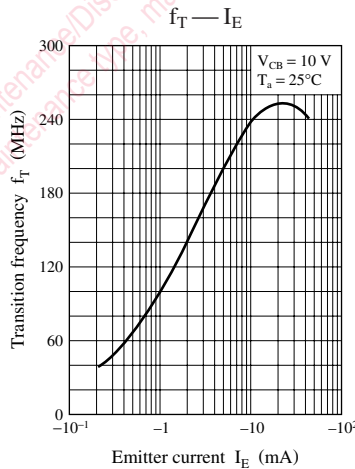
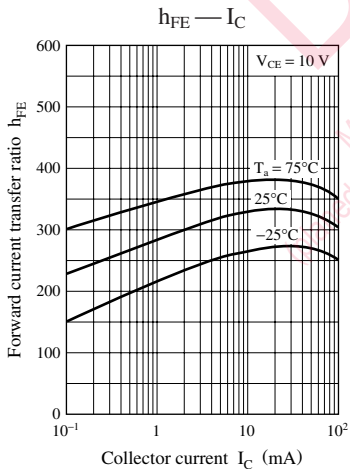
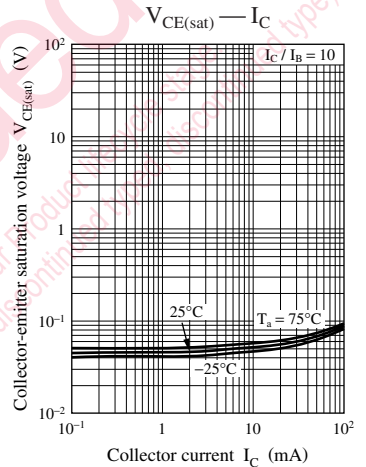
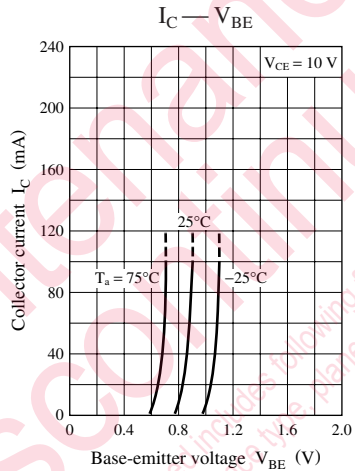
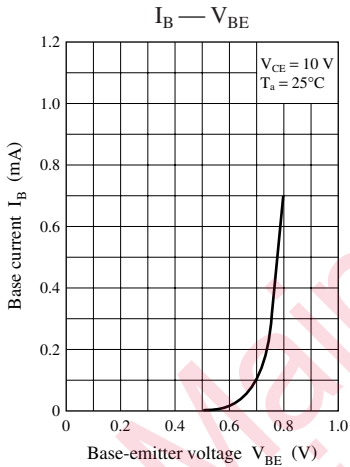
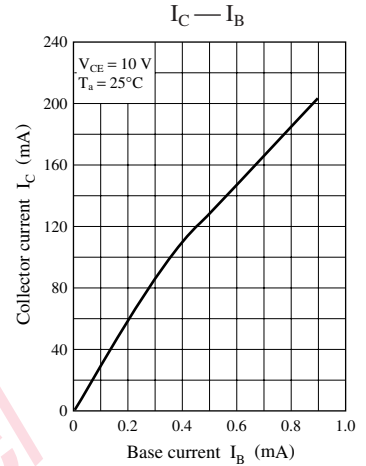
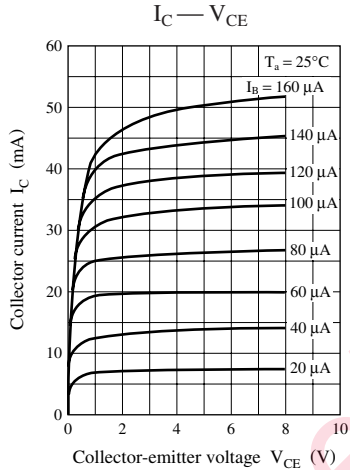
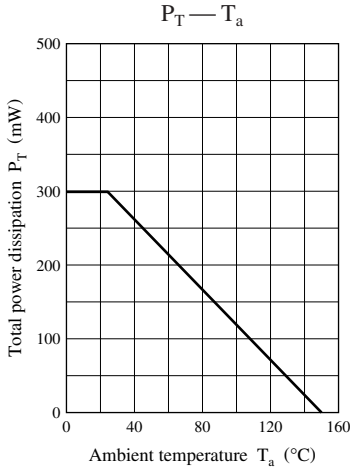


### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter   | Symbol                              | Conditions  | Min  | Typ  | Max | Unit          |
|---|-------------------------------------|---|------|------|-----|---------------|
| Collector-base voltage (Emitter open)                               | $V_{\text{CBO}}$                    | $I_{\text{C}} = 10 \mu\text{A}$ , $I_{\text{E}} = 0$                                    | 60   |      |     | V             |
| Collector-emitter voltage (Base open)                               | $V_{\text{CEO}}$                    | $I_{\text{C}} = 2 \text{ mA}$ , $I_{\text{B}} = 0$                                      | 50   |      |     | V             |
| Emitter-base voltage (Collector open)                               | $V_{\text{EBO}}$                    | $I_{\text{E}} = 10 \mu\text{A}$ , $I_{\text{C}} = 0$                                    | 7    |      |     | V             |
| Collector-base cutoff current (Emitter open)                        | $I_{\text{CBO}}$                    | $V_{\text{CB}} = 20 \text{ V}$ , $I_{\text{E}} = 0$                                     |      |      | 0.1 | $\mu\text{A}$ |
| Collector-emitter cutoff current (Base open)                        | $I_{\text{CEO}}$                    | $V_{\text{CE}} = 10 \text{ V}$ , $I_{\text{B}} = 0$                                     |      |      | 100 | $\mu\text{A}$ |
| Forward current transfer ratio                                      | $h_{\text{FE}}$                     | $V_{\text{CE}} = 10 \text{ V}$ , $I_{\text{C}} = 2 \text{ mA}$                          | 160  |      | 460 | —             |
| $h_{\text{FE}}$ ratio *   | $h_{\text{FE}}(\text{Small/Large})$ | $V_{\text{CE}} = 10 \text{ V}$ , $I_{\text{C}} = 2 \text{ mA}$                          | 0.50 | 0.99 |     | —             |
| Collector-emitter saturation voltage                                | $V_{\text{CE(sat)}}$                | $I_{\text{C}} = 100 \text{ mA}$ , $I_{\text{B}} = 10 \text{ mA}$                        |      | 0.1  | 0.3 | V             |
| Transition frequency  | $f_{\text{T}}$                      | $V_{\text{CB}} = 10 \text{ V}$ , $I_{\text{E}} = -2 \text{ mA}$ , $f = 200 \text{ MHz}$ |      | 150  |     | MHz           |
| Collector output capacitance<br>(Common base, input open circuited) | $C_{\text{ob}}$                     | $V_{\text{CB}} = 10 \text{ V}$ , $I_{\text{E}} = 0$ , $f = 1 \text{ MHz}$               |      | 3.5  |     | pF            |

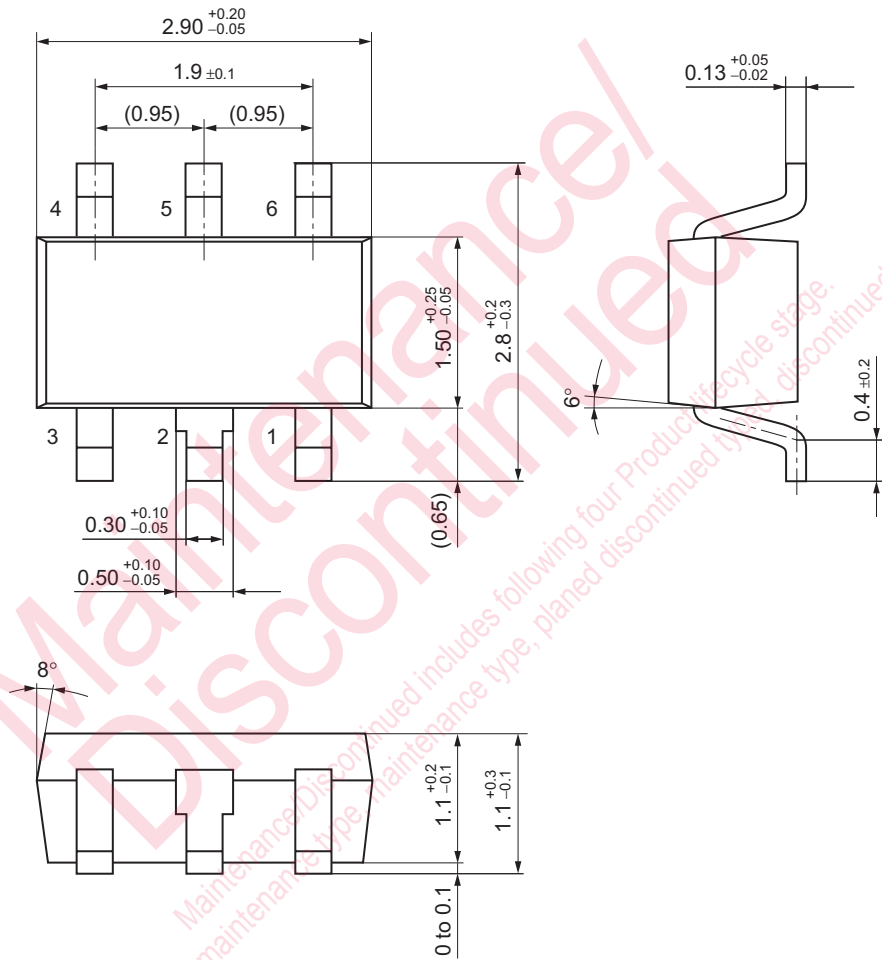
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Ratio between 2 elements



Mini6-G3

Unit: mm



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